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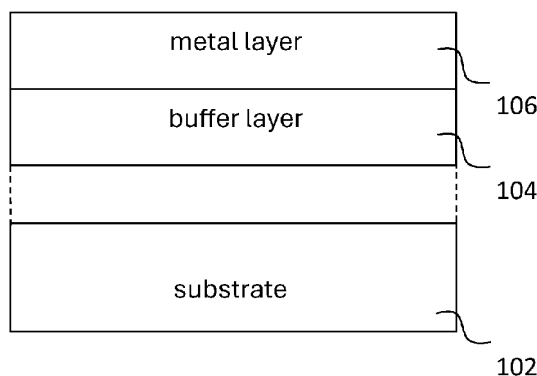
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(54) Title: STACKED ARRANGEMENT AND METHOD OF FORMING THE SAME

FIG. 1



(57) Abstract: Various embodiments may relate to a stacked arrangement. The stacked arrangement may include a substrate. The stacked arrangement may also include a buffer layer over the substrate, the buffer layer including zirconium nitride (ZrN). The stacked arrangement may further include a metal layer on the buffer layer. A crystal lattice orientation of the metal layer may be substantially in alignment with a crystal lattice orientation of the buffer layer.

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